

December 2013

FQH8N100C

N-Channel QFET® MOSFET

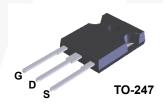
1000 V, 8.0 A, 1.45 Ω

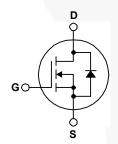
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 8 A, 1000 V, $R_{DS(on)}$ = 1.45 Ω (Max.) @ V_{GS} = 10 V
- Low Gate Charge (Typ. 53 nC)
- Low Crss (Typ. 16 pF)
- Fast Switching
- 100% Avalanche Tested
- · Improved dv/dt Capability
- · RoHS Compliant





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter	FQH8N100C	Unit
	Drain-Source Voltage	1000	V
I _D	Drain Current - Continuous (T _C = 25°C)	8.0	Α
	- Continuous (T _C = 100°C)	5.0	Α
I _{DM}	Drain Current - Pulsed	(Note 1) 32	А
V _{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2) 850	mJ
I _{AR}	Avalanche Current	(Note 1) 8.0	A
E _{AR}	Repetitive Avalanche Energy	(Note 1) 22	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3) 4.0	V/ns
P_{D}	Power Dissipation (T _C = 25°C)	225	W
	- Derate above 25°C		W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.	300	°C

Thermal Characteristics

Symbol	Parameter	FQH8N100C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.56	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	30/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQH8N100C	FQH8N100C	TO-247	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_{D} = 250 μ A	1000			V
ΔBV_{DSS} $/\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		1.4		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	/oltage Drain Current V_{DS} = 1000 V, V_{GS} = 0 V			10	μА
		V _{DS} = 800 V, T _C = 125°C			100	μА
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 4.0A		1.2	1.45	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 4.0 A		8.0		S
Dynamic C	haracteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		2475	3220	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		195	255	pF
C _{rss}	Reverse Transfer Capacitance			16	21	pF
Switching (Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 500 V, I _D = 8.0A,		50	110	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		95	200	ns
t _{d(off)}	Turn-Off Delay Time			122	254	ns
t _f	Turn-Off Fall Time	(Note 4)	/	80	170	ns
Qg	Total Gate Charge	$V_{DS} = 800 \text{ V}, I_{D} = 8.0\text{A},$		53	70	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	/	13		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		23		nC
Drain-Sour	ce Diode Characteristics and Maximum Ratings	5		I		
Maximum Continuous Drain-Source Diode Forward Current					8.0	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				32.0	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 8.0 \text{ A}$			1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_S = 8.0 \text{ A},$	45	620	//	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		5.2		μС

Notes

^{1.} Repetitive rating : pulse-width limited by maximum junction temperature.

^{2.} L = 25 mH, I_{AS} = 8.0 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.

^{3.} I $_{SD} \le 8.0$ A, di/dt ≤ 200 A/ μs , V $_{DD} \le BV _{DSS,}$ Starting T $_{J}$ = 25°C.

^{4.} Essentially independent of operating temperature.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

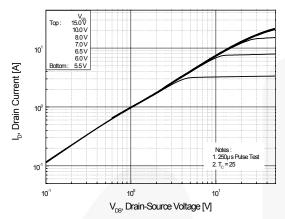


Figure 3. On-Resistance Variation vs. **Drain Current and Gate Voltage**

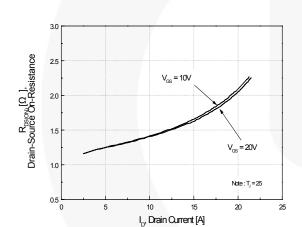


Figure 5. Capacitance Characteristics

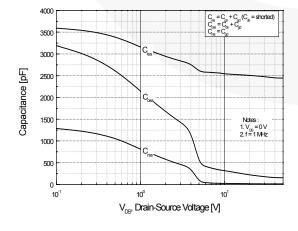


Figure 2. Transfer Characteristics

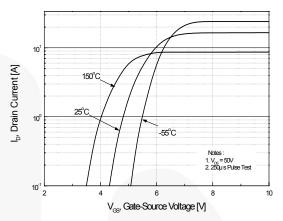


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

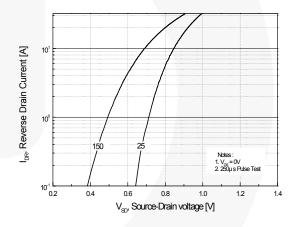
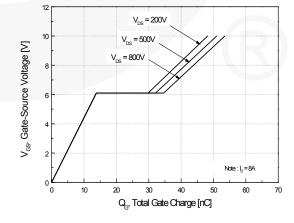


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

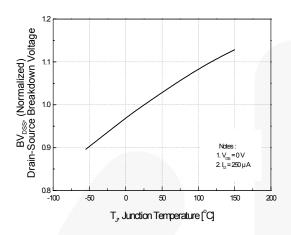


Figure 8. On-Resistance Variation vs. Temperature

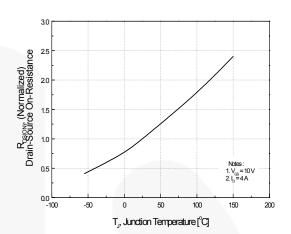
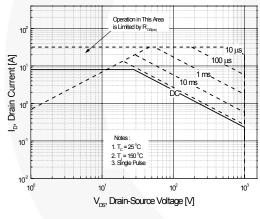


Figure 9. Maximum Safe Operating Area





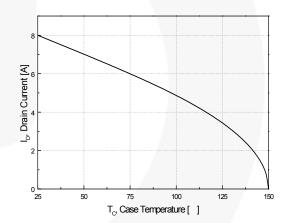
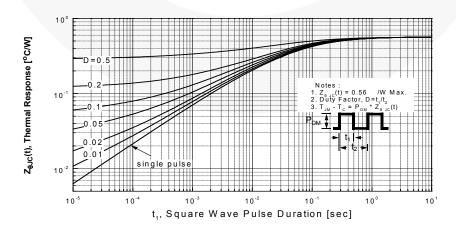


Figure 11. Transient Thermal Response Curve



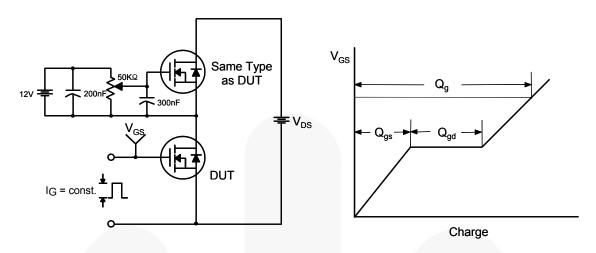


Figure 12. Gate Charge Test Circuit & Waveform

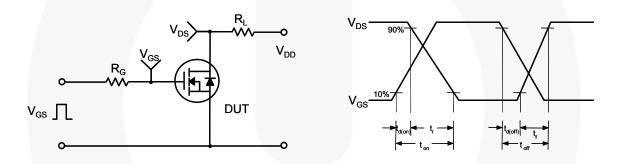


Figure 13. Resistive Switching Test Circuit & Waveforms

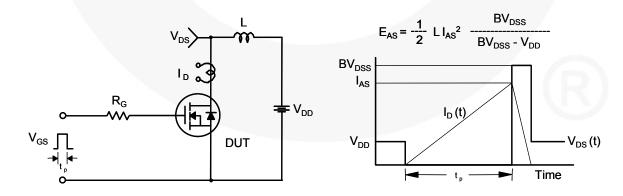


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

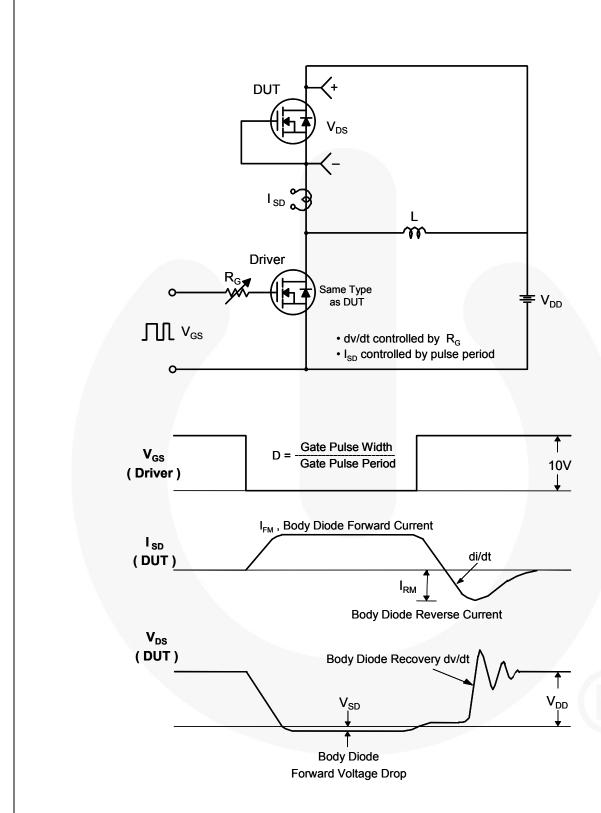
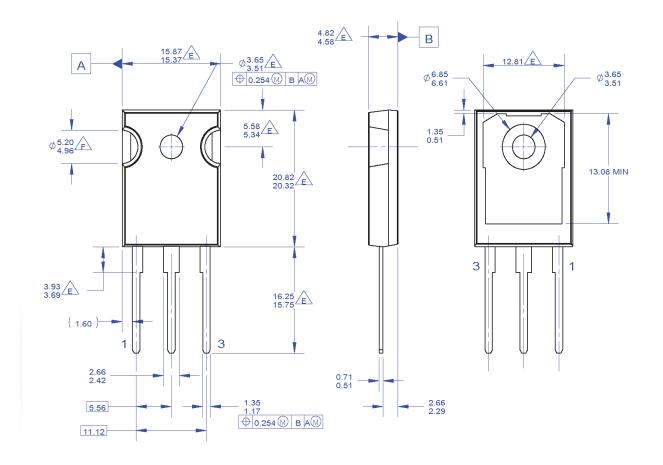


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

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- E DOES NOT COMPLY JEDEC STANDARD VALUE
- NOTCH MAY BE SQUARE
- G. DRAWING FILENAME: MKT-TO247A03_REV03

Figure 16. TO-247, Molded, 3-Lead, Jedec Variation AB

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